

E Series Power MOSFET



RoHS
COMPLIANT
HALOGEN
FREE

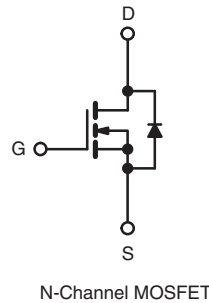
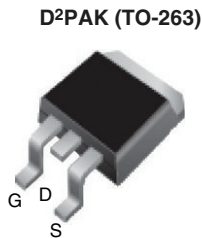
PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	550
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10\text{ V}$ 0.380
Q_g max. (nC)	50
Q_{gs} (nC)	6
Q_{gd} (nC)	10
Configuration	Single

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Computing
 - PC silver box / ATX power supplies
- Lighting
 - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
 - Power factor correction (PFC)
 - Two switch forward converter
 - Flyback converter
- Switch mode power supplies (SMPS)



ORDERING INFORMATION	
Package	D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHB12N50E-GE3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	500	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current ($T_J = 150\text{ °C}$)	V_{GS} at 10 V	$T_C = 25\text{ °C}$	10.5	A
		$T_C = 100\text{ °C}$	6.6	
Pulsed Drain Current ^a	I_{DM}	21		
Linear Derating Factor		0.91	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	103	mJ	
Maximum Power Dissipation	P_D	114	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C	
Drain-Source Voltage Slope	$V_{DS} = 0\text{ V to } 80\% V_{DS}$	dV/dt	70	V/ns
Reverse Diode dV/dt ^d			27	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ °C}$, $L = 28.2\text{ mH}$, $R_g = 25\ \Omega$, $I_{AS} = 2.7\text{ A}$.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100\text{ A}/\mu\text{s}$, starting $T_J = 25\text{ °C}$.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.1	



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	500	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA	-	0.60	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = ± 30 V	-	-	± 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C	-	-	10	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 6 A	-	0.330	0.380	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30 V, I _D = 6 A	-	3.1	-	S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz	-	886	-	pF
Output Capacitance	C _{oss}		-	52	-	
Reverse Transfer Capacitance	C _{rss}		-	6	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}		-	45	-	
Effective Output Capacitance, Time Related ^b	C _{o(tr)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	131	-	
Total Gate Charge	Q _g	V _{GS} = 10 V, I _D = 6 A, V _{DS} = 400 V	-	25	50	nC
Gate-Source Charge	Q _{gs}		-	6	-	
Gate-Drain Charge	Q _{gd}		-	10	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 400 V, I _D = 6 A, V _{GS} = 10 V, R _g = 9.1 Ω	-	13	26	ns
Rise Time	t _r		-	16	32	
Turn-Off Delay Time	t _{d(off)}		-	29	58	
Fall Time	t _f		-	12	24	
Gate Input Resistance	R _g		f = 1 MHz, open drain	-	0.92	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	10.5	A
Pulsed Diode Forward Current	I _{SM}		-	-	21	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 7.5 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 6 A, dI/dt = 100 A/μs, V _R = 25 V	-	244	-	ns
Reverse Recovery Charge	Q _{rr}		-	2.5	-	μC
Reverse Recovery Current	I _{RRM}		-	19	-	A

Notes

- a. C_{oss(er)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}.
- b. C_{oss(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

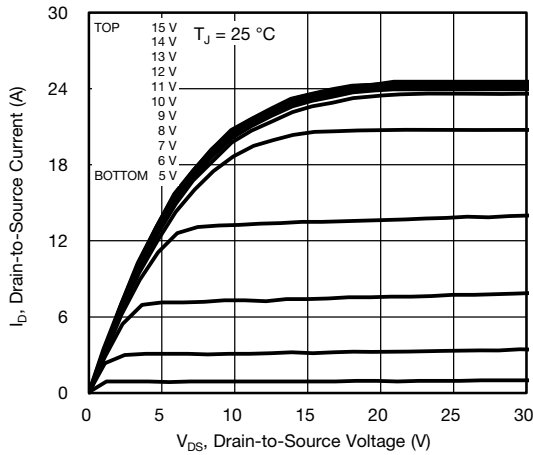


Fig. 1 - Typical Output Characteristics

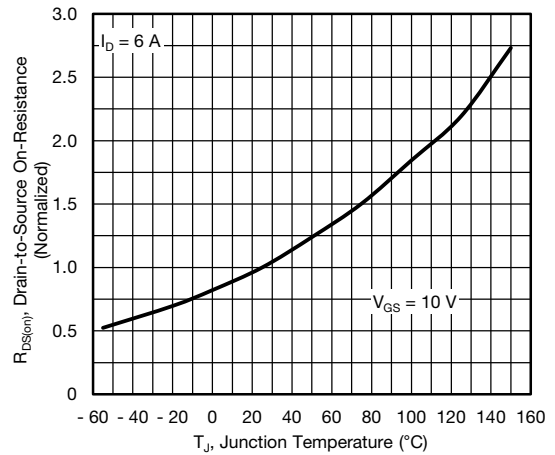


Fig. 4 - Normalized On-Resistance vs. Temperature

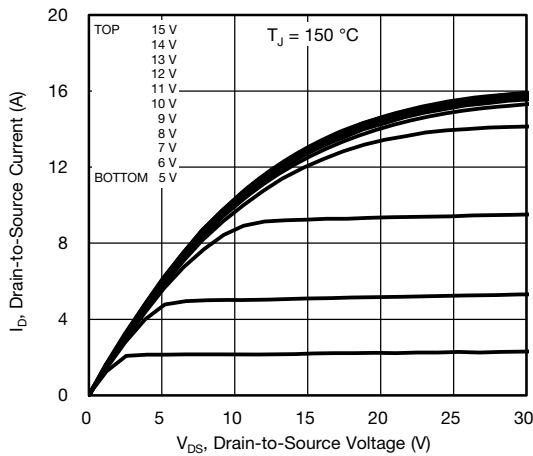


Fig. 2 - Typical Output Characteristics

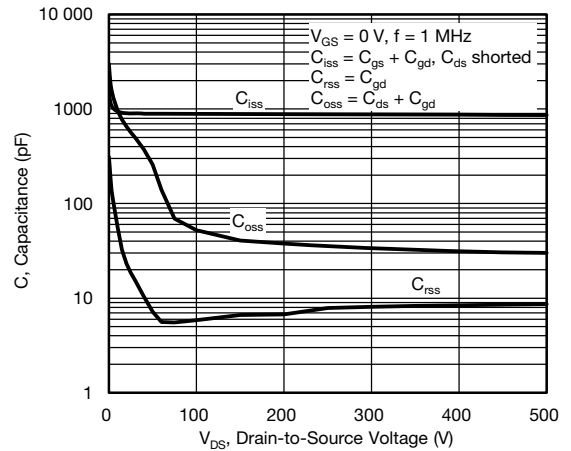


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

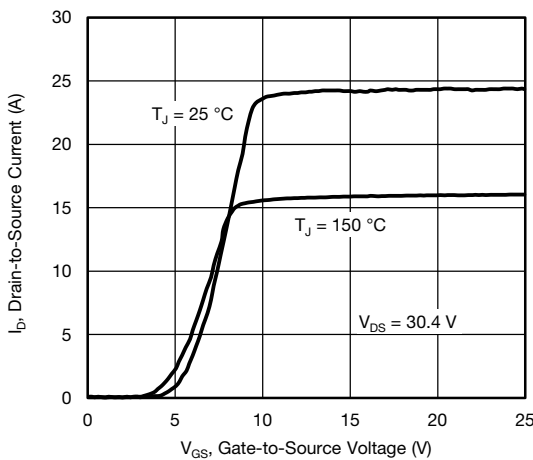


Fig. 3 - Typical Transfer Characteristics

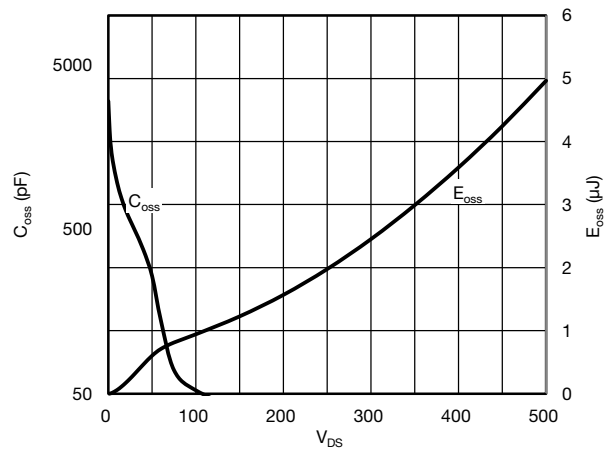


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

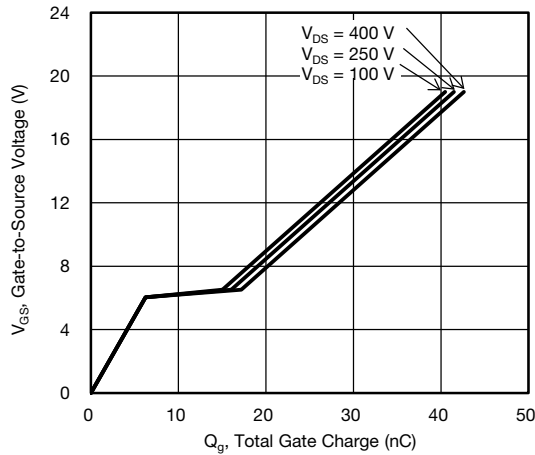


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

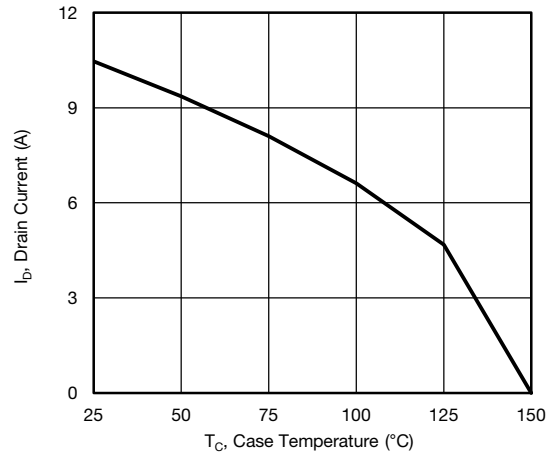


Fig. 10 - Maximum Drain Current vs. Case Temperature

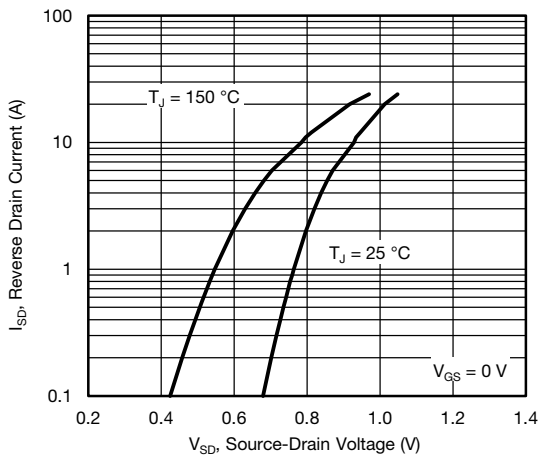


Fig. 8 - Typical Source-Drain Diode Forward Voltage

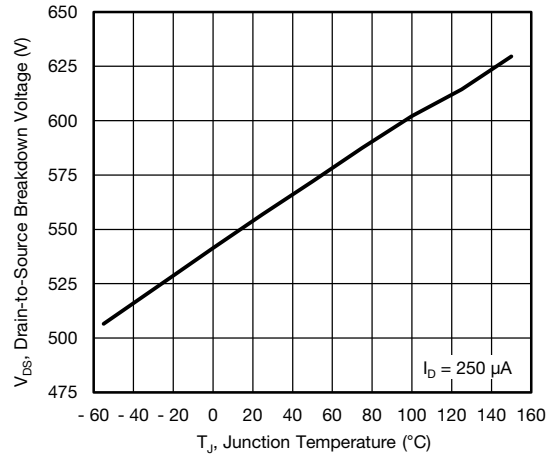


Fig. 11 - Temperature vs. Drain-to-Source Voltage

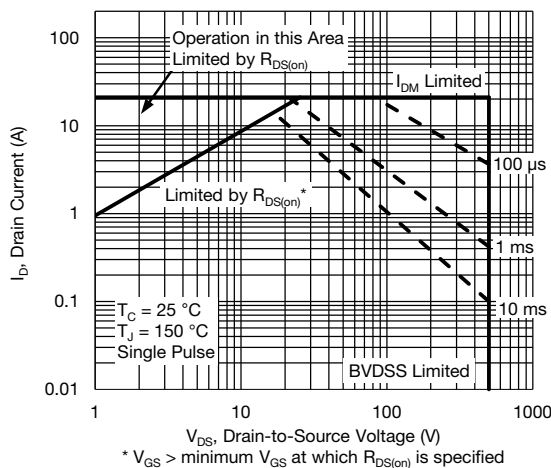


Fig. 9 - Maximum Safe Operating Area

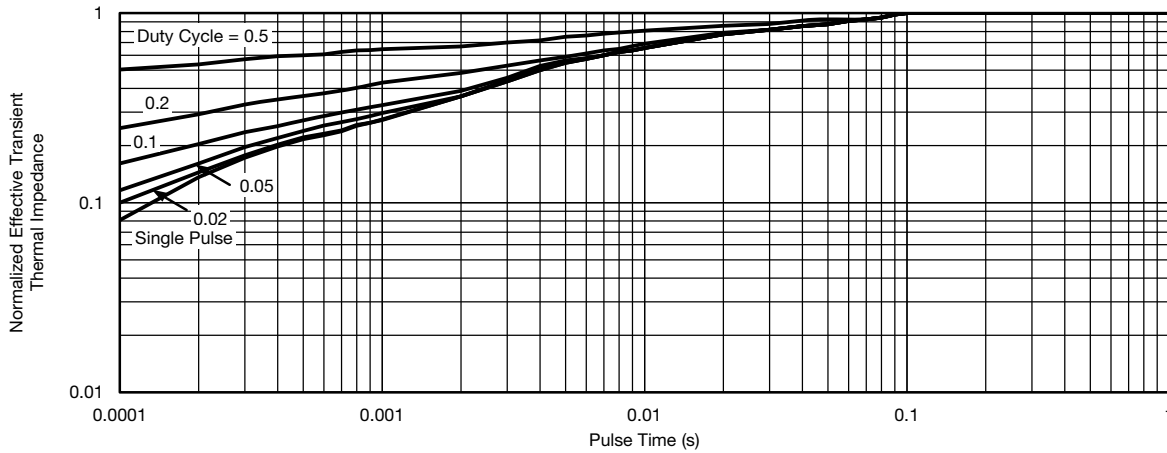


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

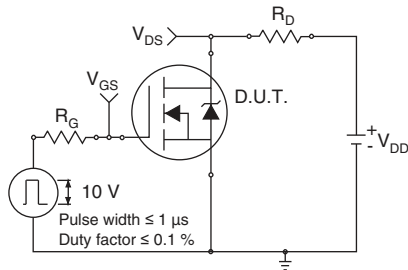


Fig. 13 - Switching Time Test Circuit

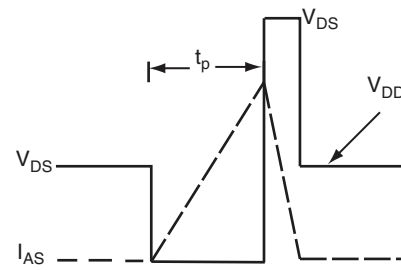


Fig. 16 - Unclamped Inductive Waveforms

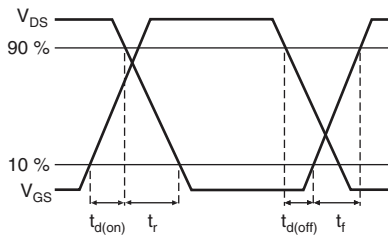


Fig. 14 - Switching Time Waveforms

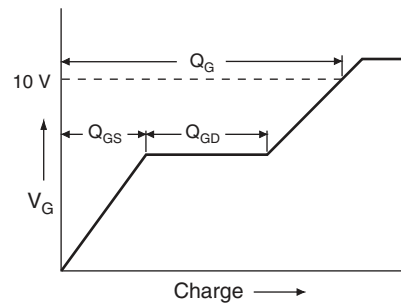


Fig. 17 - Basic Gate Charge Waveform

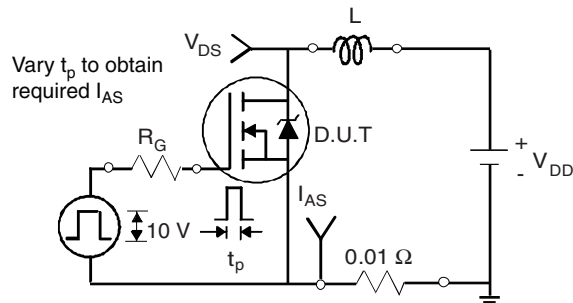


Fig. 15 - Unclamped Inductive Test Circuit

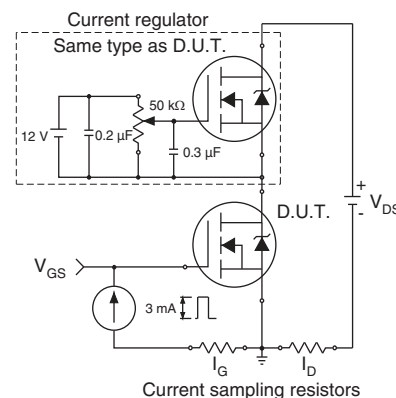


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 19 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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